

IN THE CLAIMS

Please amend the following claims.

1. (currently amended) A chemical-mechanical polishing slurry for a copper based metal layer on a semiconductor substrate, the chemical-mechanical polishing slurry comprising:
- a liquid;
 - ~~cerium ions~~ as an oxidizer in the liquid, the oxidizer comprising a complex double salt of cerium ~~the cerium ions being in a quantity equal to the inclusion of at least 0.02 molar ammonium cerium nitrate in the liquid;~~
 - an abrasive in the liquid, the liquid, the complex double salt of cerium ~~cerium ions~~ and the abrasive together having a first pH value;
 - a pH increasing glycine substance in the liquid that increases the first pH value to a second pH value above 1.5 and below 3.0; and
 - an anti-oxidizing BTA agent.
2. (currently amended) The slurry of claim 1 wherein the complex double salt of cerium comprises ammonium cerium nitrate ((NH₄)₂Ce(NO₃)₆) comprising cerium ions in quantity equal to the inclusion of between 0.05 molar and 0.1 molar of ammonium cerium nitrate.
3. (currently amended) The slurry of claim 2 wherein a concentration of ammonium cerium nitrate is at least 0.02 molar in the liquid ~~1 comprising between 1 percent and 30 percent abrasive by weight.~~
4. (original) The slurry of claim 1 wherein the abrasive is silica.
5. (previously presented) The slurry of claim 1 wherein the second pH value is at least 2.5.
6. (cancelled)
7. (currently amended) The slurry of claim 2 wherein a concentration of ammonium cerium nitrate is between 0.05 molar and 0.1 molar in the liquid ~~1 which is environmentally green.~~

8. (cancelled)

9. (cancelled)

10-11. (cancelled)

7 12. (currently amended) The slurry of claim ~~[[11]]~~ 1 comprising between 0.00200 molar and 0.00500 molar BTA.

8 13. (currently amended) The slurry of claim 1 wherein the complex double salt of cerium comprises ammonium cerium sulfate $(\text{NH}_4)_4\text{Ce}(\text{SO}_4)_4 \cdot 2\text{H}_2\text{O}$ ~~comprising cerium ions in quantity equal to between 0.02 molar and 0.1 molar ammonium cerium nitrate and BTA comprising between 0.00200 and 0.00500 molar BTA.~~

9 14. (original) The slurry of claim 13 wherein the second pH value is at least 2.5.

15-25 (cancelled)

10 26. (currently amended) A chemical-mechanical polishing slurry for polishing a copper based metal, the chemical-mechanical polishing slurry comprising:

- a liquid;
- an oxidizer comprising a complex double salt of cerium ~~cerium ions in a quantity equal to the inclusion of at least 0.02 molar ammonium cerium nitrate in the liquid;~~
- an abrasive in the liquid;
- benzotriazole (BTA) in the liquid to inhibit corrosion; and
- a glycine complexing agent in the liquid and to increase a pH value of the slurry to above 1.5 and below 3.0.

11 27. (original) The slurry of claim 26, comprising between 0.00100 molar and 0.00500 molar benzotriazole (BTA).

12/28. (original) The slurry of claim 26, comprising between 1 and 3 percent glycine by weight.

13/29. (original) The slurry of claim 26, wherein the liquid is deionized liquid water.